

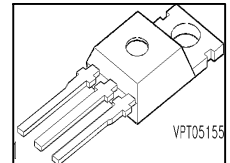
Cool MOS™ Power Transistor

Feature

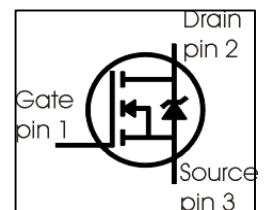
- New revolutionary high voltage technology
- Ultra low gate charge
- Periodic avalanche rated
- Extreme dv/dt rated
- High peak current capability
- Intrinsic fast-recovery body diode
- Extreme low reverse recovery charge
- Pb-free lead palting; RoHS compliant, Halogen free mold compound
- Qualified for industrial grade applications according to JEDEC⁰⁾

$V_{DS} @ T_{jmax}$	650	V
$R_{DS(on)}$	0.44	Ω
I_D	11	A

PG-TO220



Type	Package	Ordering Code	Marking
SPP11N60CFD	PG-TO220	Q67040-S4618	11N60CFD



Maximum Ratings

Parameter	Symbol	Value	Unit
Continuous drain current $T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$	I_D	11 7	A
Pulsed drain current, t_p limited by T_{jmax}	$I_{D \text{ puls}}$	28	
Avalanche energy, single pulse $I_D = 5.5 \text{ A}$, $V_{DD} = 50 \text{ V}$	E_{AS}	340	mJ
Avalanche energy, repetitive t_{AR} limited by $T_{jmax}^{1)}$ $I_D = 11 \text{ A}$, $V_{DD} = 50 \text{ V}$	E_{AR}	0.6	
Avalanche current, repetitive t_{AR} limited by T_{jmax}	I_{AR}	11	A
Reverse diode dv/dt $I_S = 11 \text{ A}$, $V_{DS} = 480 \text{ V}$, $T_j = 125^\circ\text{C}$	dv/dt	40	V/ns
Gate source voltage	V_{GS}	± 20	V
Gate source voltage AC ($f > 1 \text{ Hz}$)	V_{GS}	± 30	
Power dissipation, $T_C = 25^\circ\text{C}$	P_{tot}	125	W
Operating and storage temperature	T_j, T_{stg}	-55... +150	$^\circ\text{C}$

Maximum Ratings

Parameter	Symbol	Value	Unit
Drain Source voltage slope $V_{DS} = 480 \text{ V}$, $I_D = 11 \text{ A}$, $T_j = 125^\circ\text{C}$	dv/dt	80	V/ns
Maximum diode commutation speed $V_{DS} = 480 \text{ V}$, $I_D = 11 \text{ A}$, $T_j = 125^\circ\text{C}$	di_F/dt	600	A/ μs

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Thermal resistance, junction - case	R_{thJC}	-	-	1	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	62	
Soldering temperature, wavesoldering 1.6 mm (0.063 in.) from case for 10s	T_{sold}	-	-	260	$^\circ\text{C}$

Electrical Characteristics, at $T_j=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{V}$, $I_D=0.25\text{mA}$	600	-	-	V
Drain-Source avalanche breakdown voltage	$V_{(BR)DS}$	$V_{GS}=0\text{V}$, $I_D=11\text{A}$	-	700	-	
Gate threshold voltage	$V_{GS(th)}$	$I_D=500\mu\text{A}$, $V_{GS}=V_{DS}$	3	4	5	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=600\text{V}$, $V_{GS}=0\text{V}$, $T_j=25^\circ\text{C}$, $T_j=150^\circ\text{C}$	- -	1.1 900	- -	μA
Gate-source leakage current	I_{GSS}	$V_{GS}=20\text{V}$, $V_{DS}=0\text{V}$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{V}$, $I_D=7\text{A}$, $T_j=25^\circ\text{C}$, $T_j=150^\circ\text{C}$	- -	0.38 1.02	0.44 -	Ω
Gate input resistance	R_G	$f=1\text{MHz}$, open Drain	-	0.86	-	

Electrical Characteristics , at $T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Transconductance	g_{fs}	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$, $I_D = 7\text{A}$	-	8.3	-	S
Input capacitance	C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$	-	1200	-	pF
Output capacitance	C_{oss}		-	390	-	
Reverse transfer capacitance	C_{rss}		-	30	-	
Effective output capacitance, ²⁾ energy related	$C_{o(er)}$	$V_{GS} = 0\text{V}$, $V_{DS} = 0\text{V to } 480\text{V}$	-	45	-	pF
Effective output capacitance, ³⁾ time related	$C_{o(tr)}$		-	85	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 380\text{V}$, $V_{GS} = 0/10\text{V}$, $I_D = 11\text{A}$, $R_G = 6.8\Omega$	-	34	-	ns
Rise time	t_r		-	18	-	
Turn-off delay time	$t_{d(off)}$		-	43	-	
Fall time	t_f		-	7	-	

Gate Charge Characteristics

Gate to source charge	Q_{gs}	$V_{DD} = 480\text{V}$, $I_D = 11\text{A}$	-	9	-	nC
Gate to drain charge	Q_{gd}		-	23	-	
Gate charge total	Q_g	$V_{DD} = 480\text{V}$, $I_D = 11\text{A}$, $V_{GS} = 0 \text{ to } 10\text{V}$	-	48	64	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 480\text{V}$, $I_D = 11\text{A}$	-	7	-	V

⁰J-STD20 and JESD22

¹Repetitive avalanche causes additional power losses that can be calculated as $P_{AV} = E_{AR} \cdot f$.

² $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

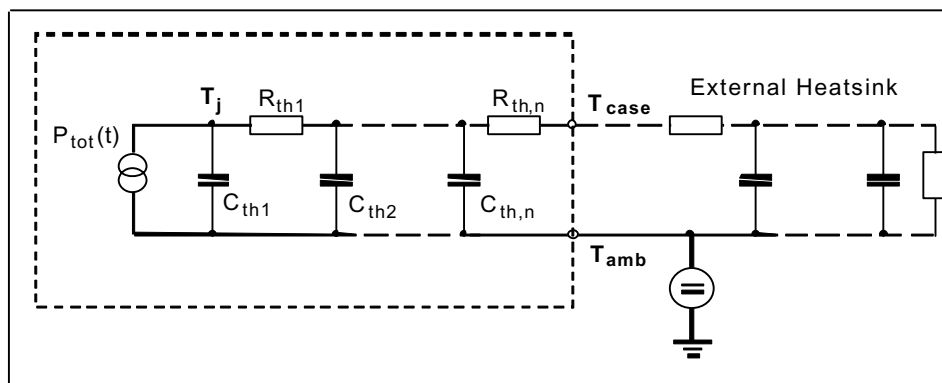
³ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

Electrical Characteristics, at $T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Inverse diode continuous forward current	I_S	$T_C=25^{\circ}\text{C}$	-	-	11	A
Inverse diode direct current, pulsed	I_{SM}		-	-	28	
Inverse diode forward voltage	V_{SD}	$V_{GS}=0\text{V}$, $I_F=I_S$	-	1	1.2	V
Reverse recovery time	t_{rr}	$V_R=480\text{V}$, $I_F=I_S$, $di_F/dt=100\text{A}/\mu\text{s}$	-	140	-	ns
Reverse recovery charge	Q_{rr}		-	0.7	-	μC
Peak reverse recovery current	I_{rrm}		-	11	-	A
Peak rate of fall of reverse recovery current	di_{rr}/dt		-	1200	-	$\text{A}/\mu\text{s}$

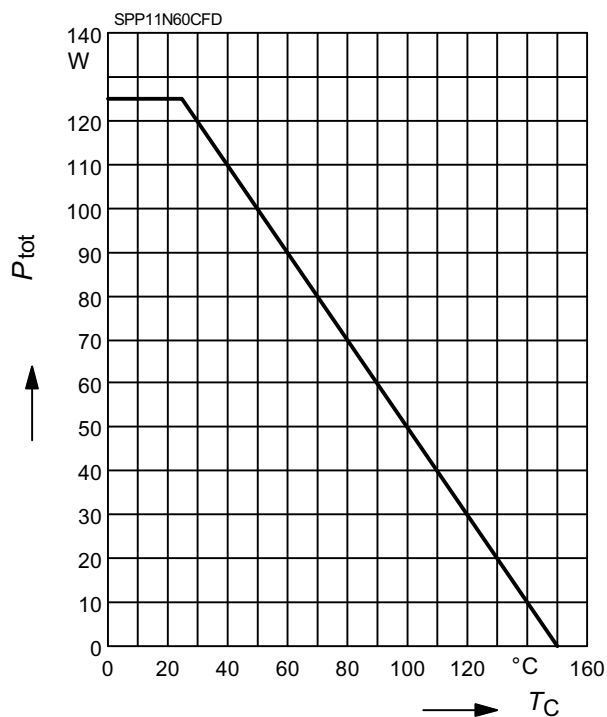
Typical Transient Thermal Characteristics

Symbol	Value	Unit	Symbol	Value	Unit
	typ.			typ.	
Thermal resistance			Thermal capacitance		
R_{th1}	0.015	K/W	C_{th1}	0.0001878	Ws/K
R_{th2}	0.03		C_{th2}	0.0007106	
R_{th3}	0.056		C_{th3}	0.000988	
R_{th4}	0.197		C_{th4}	0.002791	
R_{th5}	0.216		C_{th5}	0.007285	
R_{th6}	0.083		C_{th6}	0.063	



1 Power dissipation

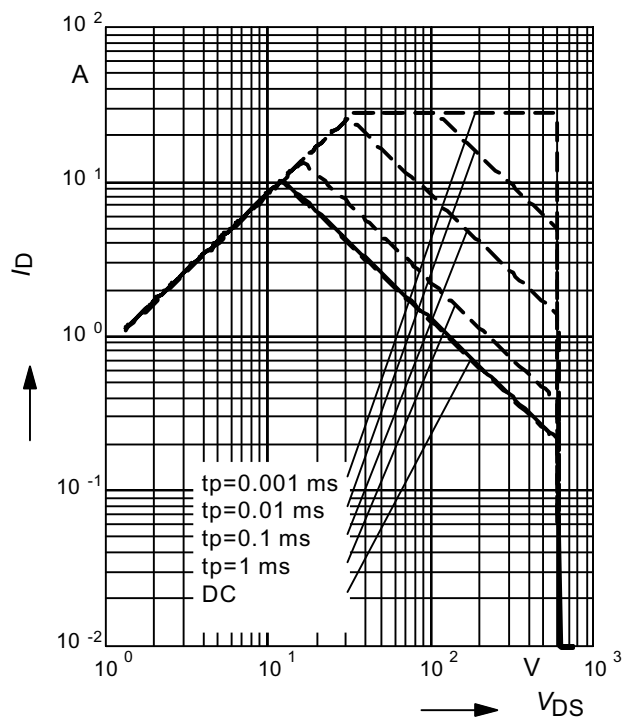
$$P_{\text{tot}} = f(T_C)$$



2 Safe operating area

$$I_D = f(V_{DS})$$

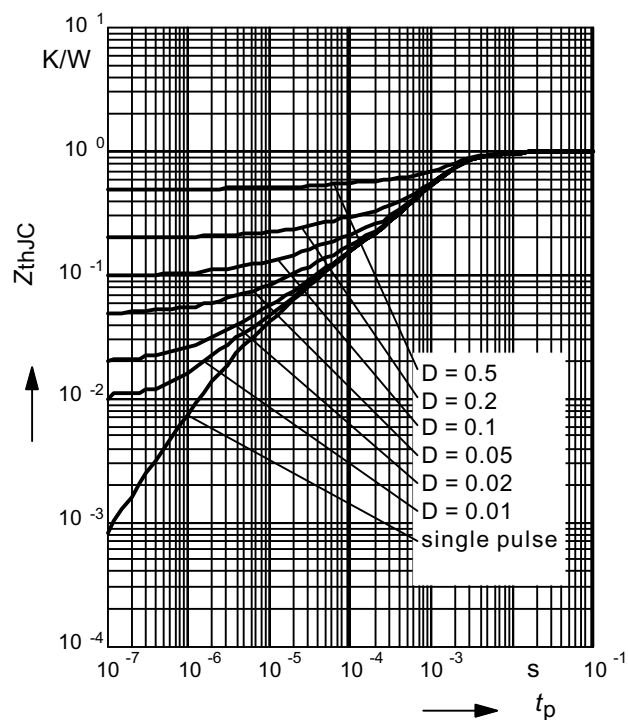
parameter : $D = 0$, $T_C = 25^\circ\text{C}$



3 Transient thermal impedance

$$Z_{\text{thJC}} = f(t_p)$$

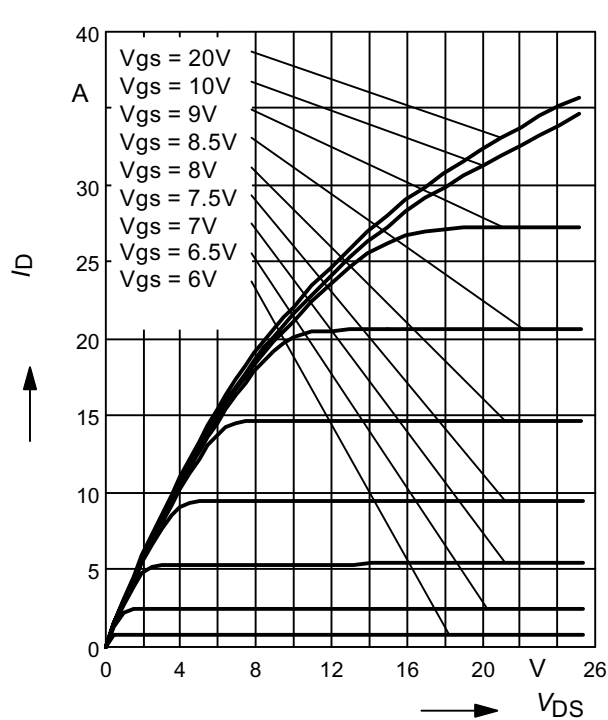
parameter: $D = t_p/T$



4 Typ. output characteristic

$$I_D = f(V_{DS}); T_J = 25^\circ\text{C}$$

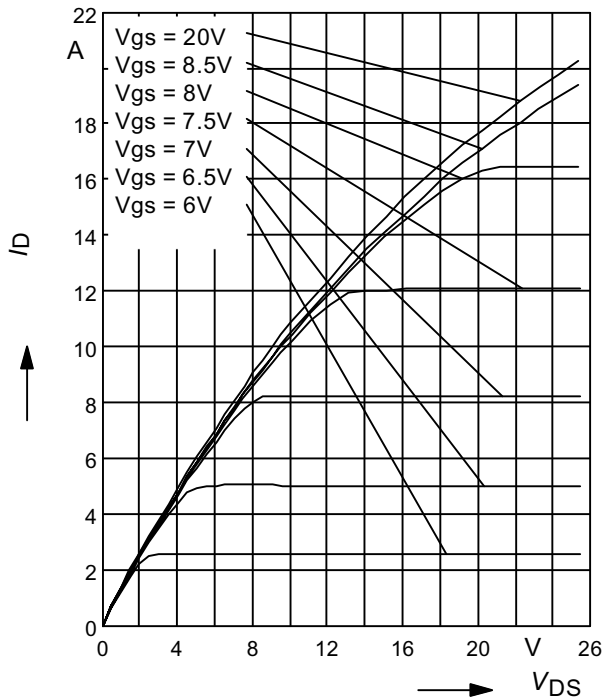
parameter: $t_p = 10 \mu\text{s}$, V_{GS}



5 Typ. output characteristic

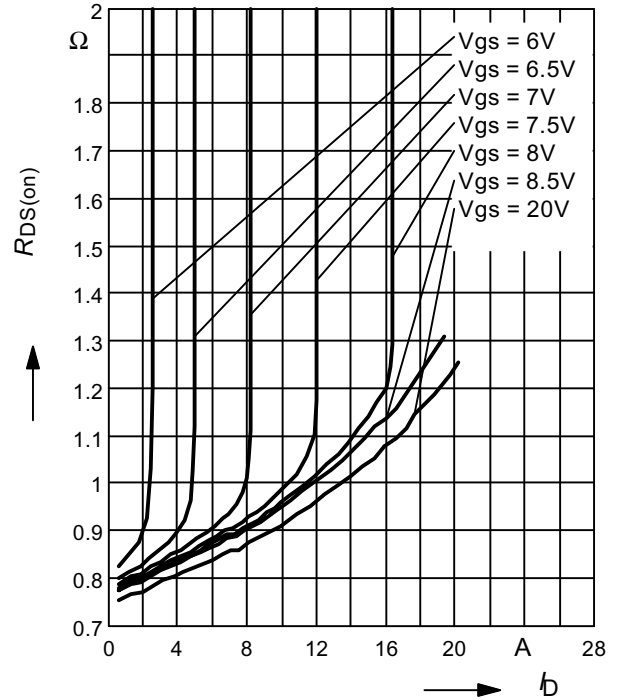
$$I_D = f(V_{DS}); T_j = 150^\circ\text{C}$$

parameter: $t_p = 10 \mu\text{s}$, V_{GS}


6 Typ. drain-source on resistance

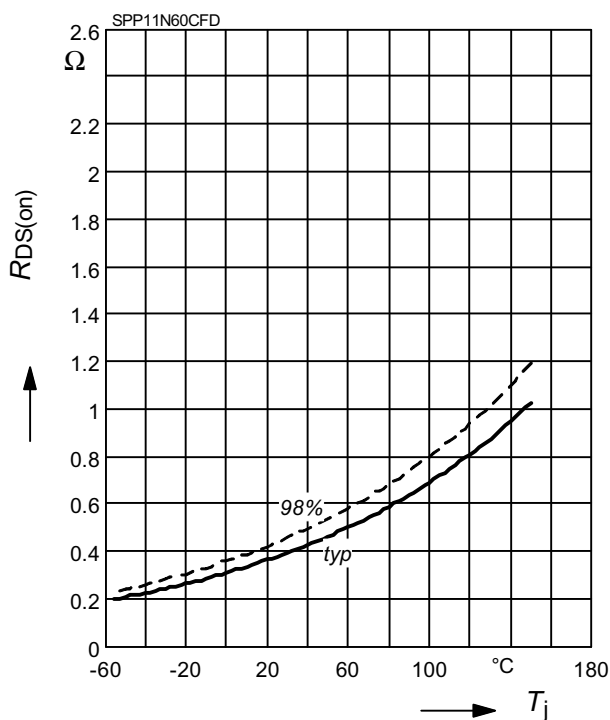
$$R_{DS(on)} = f(I_D)$$

parameter: $T_j = 150^\circ\text{C}$, V_{GS}


7 Drain-source on-state resistance

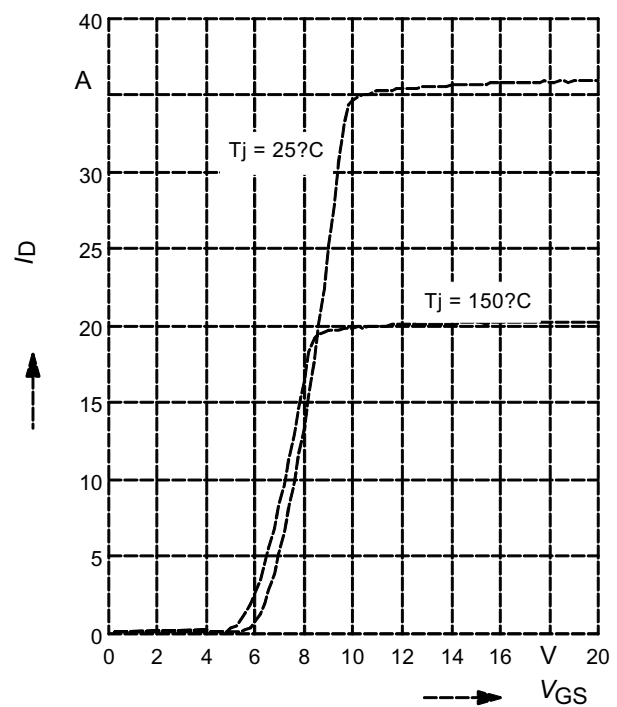
$$R_{DS(on)} = f(T_j)$$

parameter: $I_D = 7 \text{ A}$, $V_{GS} = 10 \text{ V}$


8 Typ. transfer characteristics

$$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$$

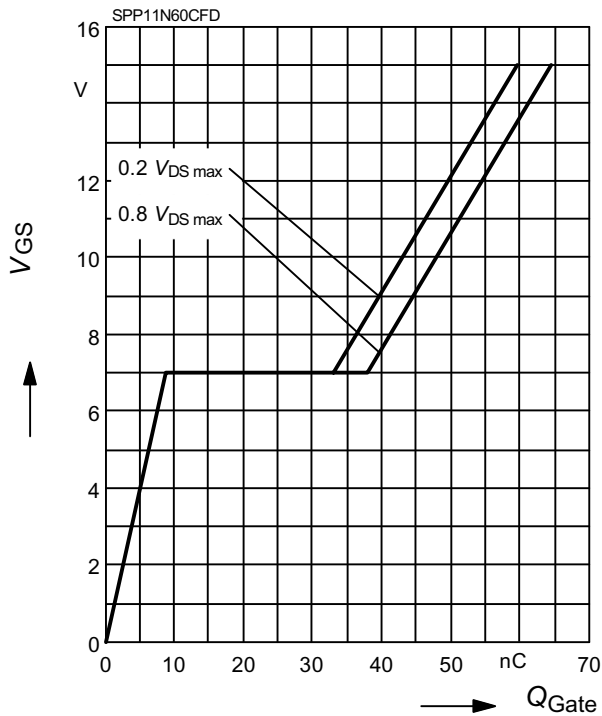
parameter: $t_p = 10 \mu\text{s}$



9 Typ. gate charge

$$V_{GS} = f(Q_{Gate})$$

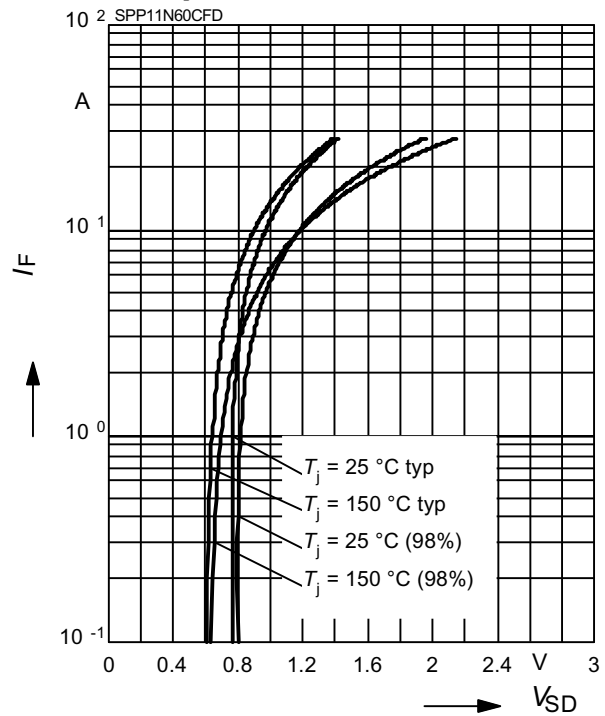
parameter: $I_D = 11\text{ A}$ pulsed



10 Forward characteristics of body diode

$$I_F = f(V_{SD})$$

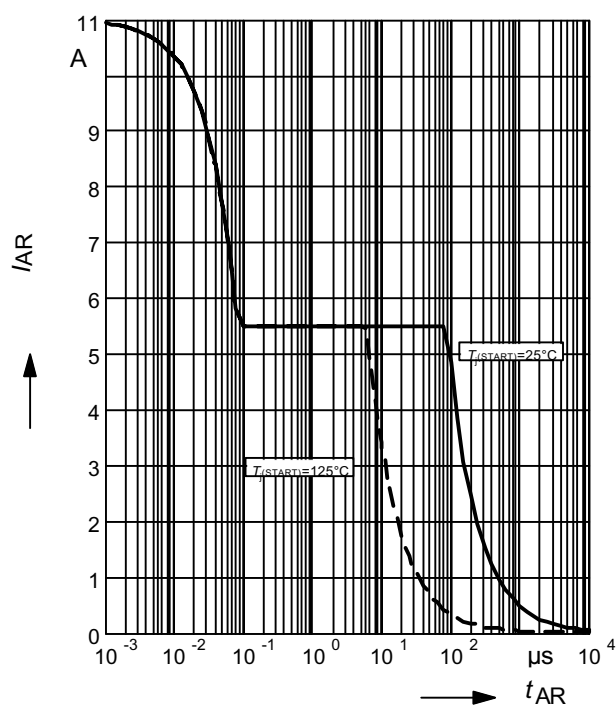
parameter: $T_j, t_p = 10\text{ }\mu\text{s}$



11 Avalanche SOA

$$I_{AR} = f(t_{AR})$$

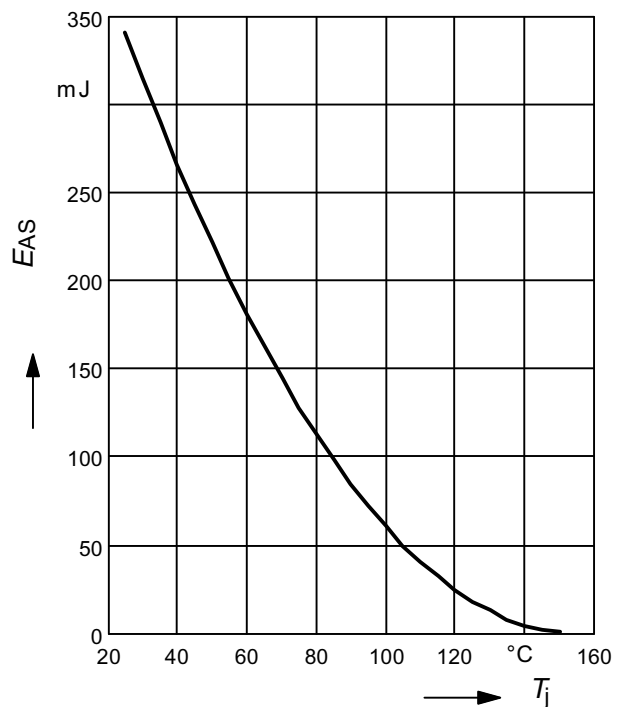
par.: $T_j \leq 150\text{ }^\circ\text{C}$



12 Avalanche energy

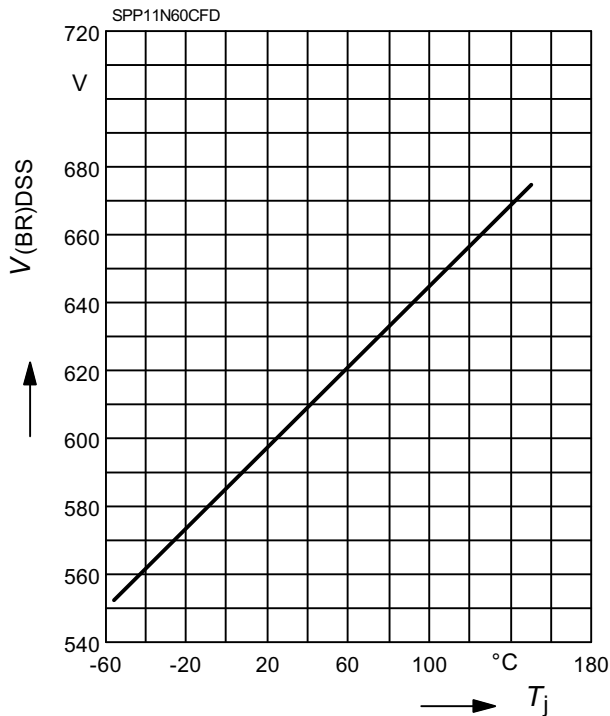
$$E_{AS} = f(T_j)$$

par.: $I_D = 5.5\text{ A}, V_{DD} = 50\text{ V}$



13 Drain-source breakdown voltage

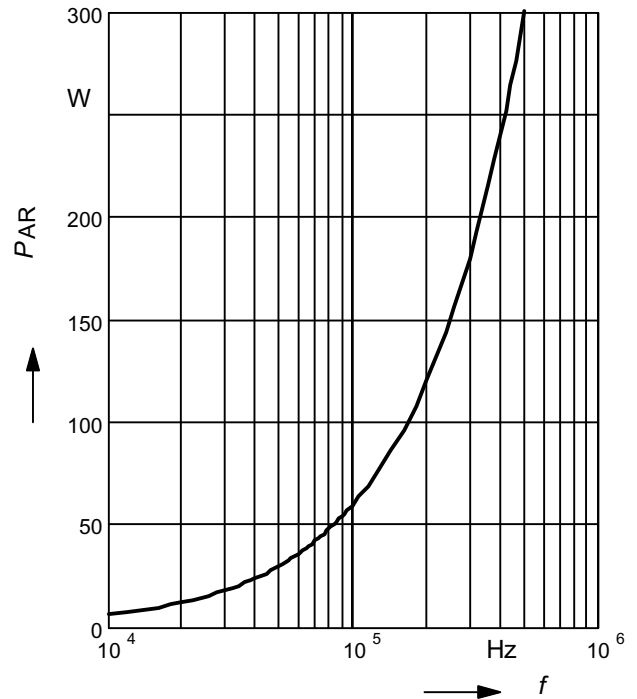
$$V_{(BR)DSS} = f(T_j)$$



14 Avalanche power losses

$$P_{AR} = f(f)$$

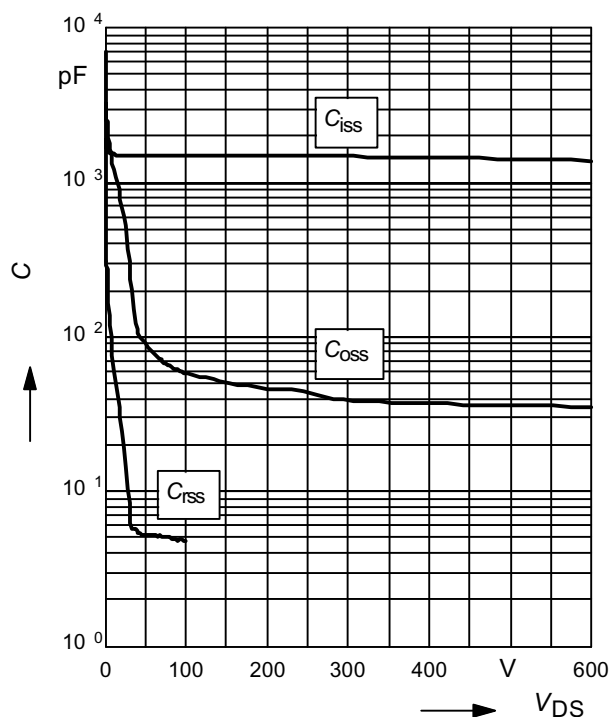
parameter: $E_{AR}=0.6\text{mJ}$



15 Typ. capacitances

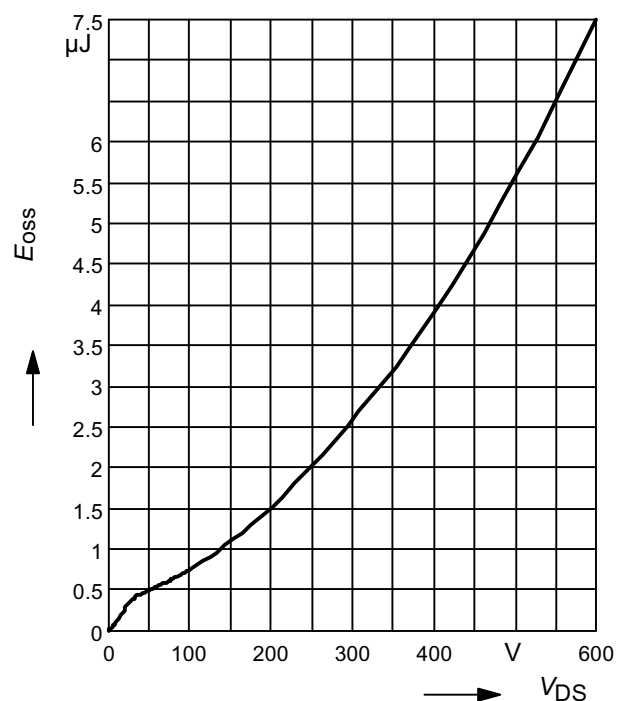
$$C = f(V_{DS})$$

parameter: $V_{GS}=0\text{V}$, $f=1\text{ MHz}$



16 Typ. C_{oss} stored energy

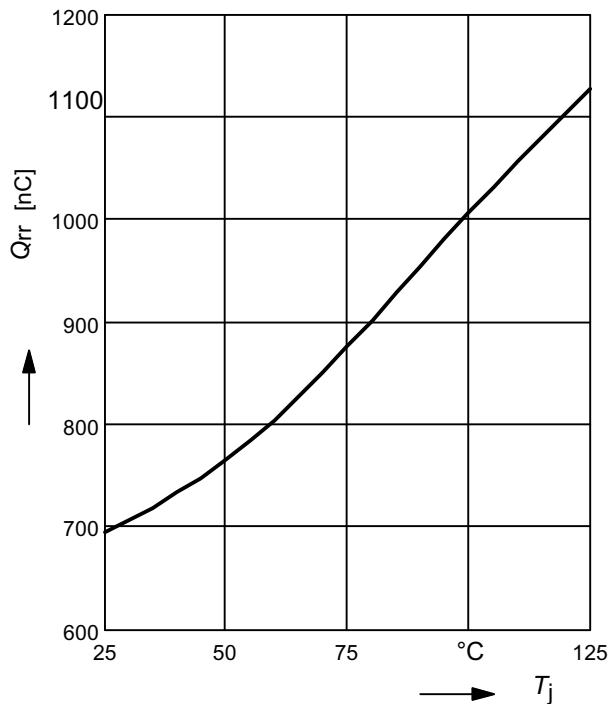
$$E_{oss}=f(V_{DS})$$



17 Typ. reverse recovery charge

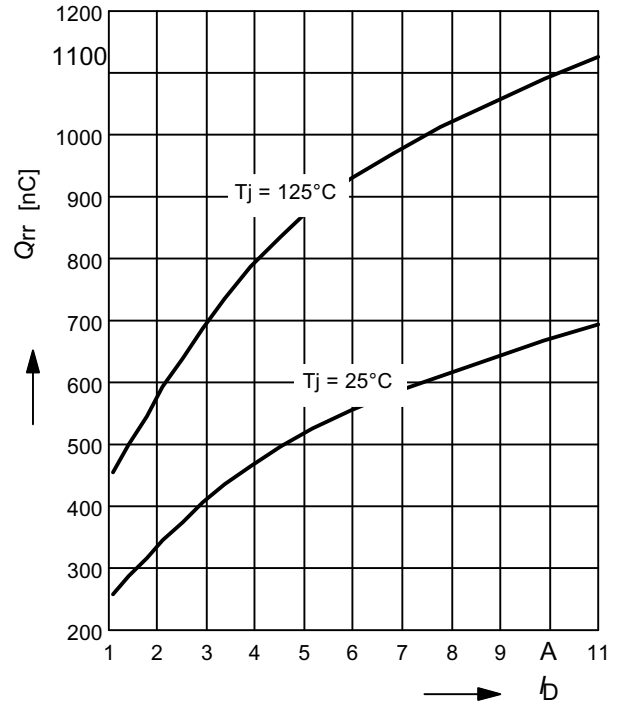
$$Q_{rr} = f(T_J)$$

parameter: $I_D = 11\text{ A}$


18 Typ. reverse recovery charge

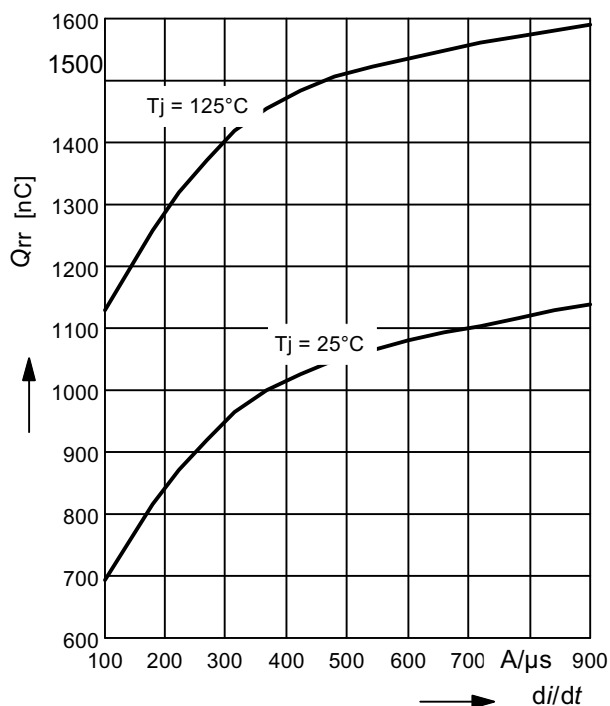
$$Q_{rr} = f(I_D)$$

parameter: $di/dt = 100\text{ A/}\mu\text{s}$

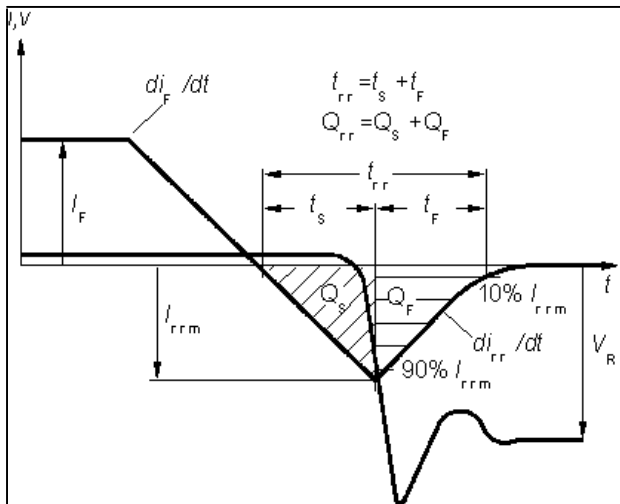

19 Typ. reverse recovery charge

$$Q_{rr} = f(di/dt)$$

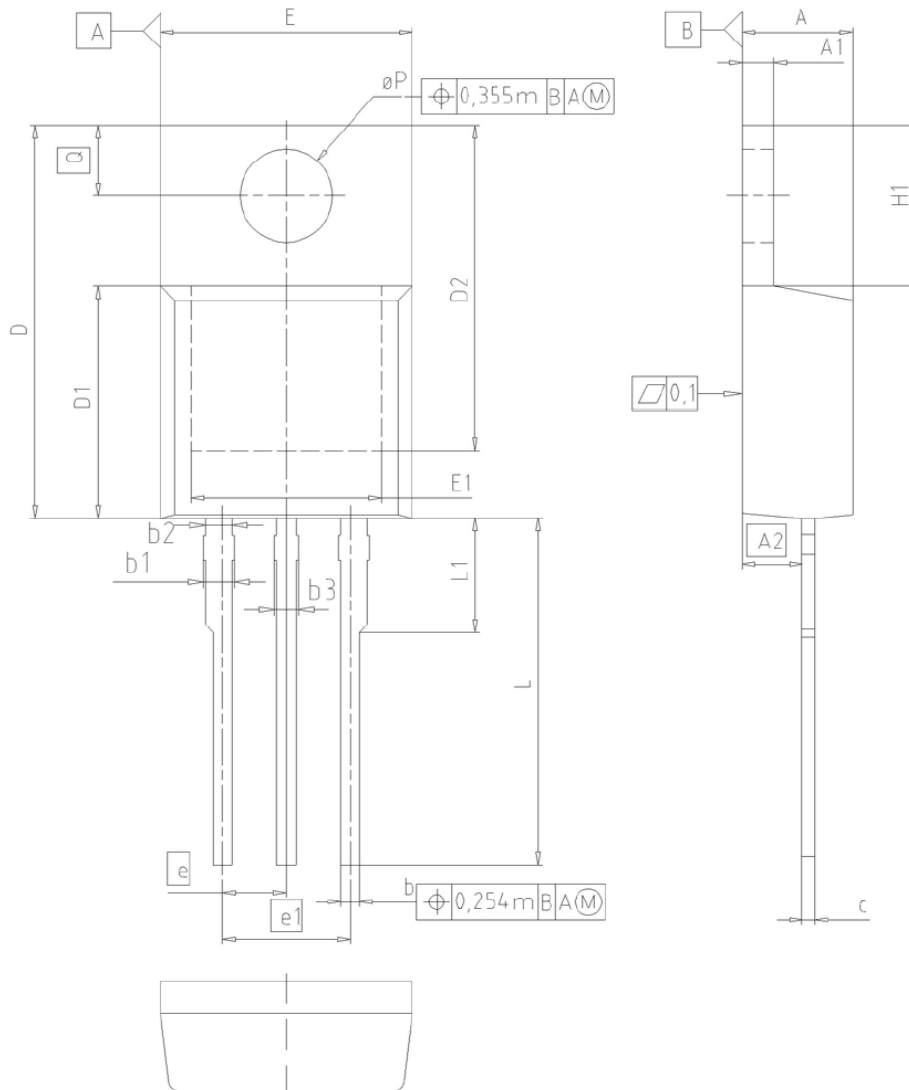
parameter: $I_D = 11\text{ A}$



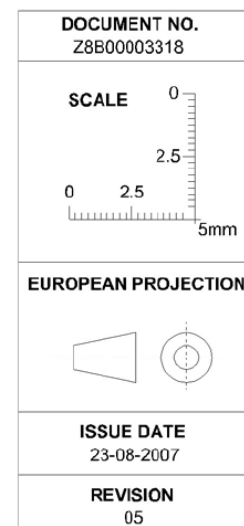
Definition of diodes switching characteristics



PG-TO-220-3-1, PG-TO220-3-21



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	1.17	1.40	0.046	0.055
A2	2.15	2.72	0.085	0.107
b	0.65	0.86	0.026	0.034
b1	0.95	1.40	0.037	0.055
b2	0.95	1.15	0.037	0.045
b3	0.65	1.15	0.026	0.045
c	0.33	0.60	0.013	0.024
D	14.81	15.95	0.583	0.628
D1	8.51	9.45	0.335	0.372
D2	12.19	13.10	0.480	0.516
E	9.70	10.36	0.382	0.408
E1	6.50	8.60	0.256	0.339
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H1	5.90	6.90	0.232	0.272
L	13.00	14.00	0.512	0.551
L1	-	4.80	-	0.189
øP	3.60	3.89	0.142	0.153
Q	2.60	3.00	0.102	0.118



Published by
Infineon Technologies AG
81726 Munich, Germany
© 2007 Infineon Technologies AG
All Rights Reserved.

Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

Information

For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office (www.infineon.com).

Warnings

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office. The Infineon Technologies component described in this Data Sheet may be used in life-support devices or systems and/or automotive, aviation and aerospace applications or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support, automotive, aviation and aerospace device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9